

## ABSTRACT OF THE DISCLOSURE

A semiconductor memory with shielding effect is disclosed in the invention. The memory includes at least a plurality of word lines, one ground line control unit, and a plurality of memory units. Every memory unit includes  
5 a primary bit line, a ground line, a first equivalent switch, and a second equivalent switch. The primary bit line is enabled by a control signal. The ground line and the ground line control unit are electrically connected. The first equivalent switch is coupled to both the primary bit line and the ground line, and is controlled by the control signal of the previous memory unit. The  
10 second equivalent switch is coupled to both the primary bit line and the ground line of the next memory unit, and is controlled by the control signal of the next memory unit.

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